

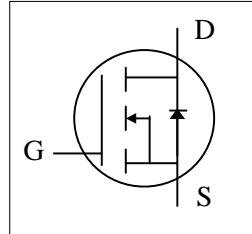
# XP10TN028YT

**Halogen-Free Product**



*N-CHANNEL ENHANCEMENT MODE  
POWER MOSFET*

- ▼ Simple Drive Requirement
- ▼ Small Size & Lower Profile
- ▼ RoHS Compliant & Halogen-Free

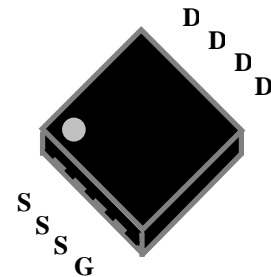


|              |              |
|--------------|--------------|
| $BV_{DSS}$   | 100V         |
| $R_{DS(ON)}$ | 28m $\Omega$ |
| $I_D$        | 7.5A         |

## Description

XP10TN028 series are innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The PMPAK<sup>®</sup> 3x3 package is special for voltage conversion application using standard infrared reflow technique with the backside heat sink to achieve the good thermal performance.



PMPAK<sup>®</sup> 3 x 3

## Absolute Maximum Ratings @ $T_J=25^{\circ}\text{C}$ (unless otherwise specified)

| Symbol                       | Parameter                                  | Rating     | Units              |
|------------------------------|--|------------|--------------------|
| $V_{DS}$                     | Drain-Source Voltage                       | 100        | V                  |
| $V_{GS}$                     | Gate-Source Voltage                        | +20        | V                  |
| $I_D@T_A=25^{\circ}\text{C}$ | Drain Current, $V_{GS}$ @ 10V <sup>3</sup> | 7.5        | A                  |
| $I_D@T_A=70^{\circ}\text{C}$ | Drain Current, $V_{GS}$ @ 10V <sup>3</sup> | 6          | A                  |
| $I_{DM}$                     | Pulsed Drain Current <sup>1</sup>          | 30         | A                  |
| $P_D@T_A=25^{\circ}\text{C}$ | Total Power Dissipation                    | 3.125      | W                  |
| $T_{STG}$                    | Storage Temperature Range                  | -55 to 150 | $^{\circ}\text{C}$ |
| $T_J$                        | Operating Junction Temperature Range       | -55 to 150 | $^{\circ}\text{C}$ |

## Thermal Data

| Symbol | Parameter   | Value | Unit                        |
|--------|---|-------|-----------------------------|
| Rthj-c | Maximum Thermal Resistance, Junction-case                 | 5     | $^{\circ}\text{C}/\text{W}$ |
| Rthj-a | Maximum Thermal Resistance, Junction-ambient <sup>3</sup> | 40    | $^{\circ}\text{C}/\text{W}$ |

**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

| Symbol              | Parameter                                      | Test Conditions  | Min. | Typ. | Max. | Units |
|---------------------|--|--|------|------|------|-------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage                 | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA               | 100  | -    | -    | V     |
| R <sub>DS(ON)</sub> | Static Drain-Source On-Resistance <sup>2</sup> | V <sub>GS</sub> =10V, I <sub>D</sub> =7A                 | -    | -    | 28   | mΩ    |
|                     |  | V <sub>GS</sub> =5V, I <sub>D</sub> =4A                  | -    | -    | 40   | mΩ    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage                         | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA | 1    | -    | 3    | V     |
| g <sub>fs</sub>     | Forward Transconductance                       | V <sub>DS</sub> =10V, I <sub>D</sub> =7A                 | -    | 20   | -    | S     |
| I <sub>DSS</sub>    | Drain-Source Leakage Current                   | V <sub>DS</sub> =80V, V <sub>GS</sub> =0V                | -    | -    | 25   | uA    |
| I <sub>GSS</sub>    | Gate-Source Leakage                            | V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V              | -    | -    | ±100 | nA    |
| Q <sub>g</sub>      | Total Gate Charge                              | I <sub>D</sub> =5A                                       | -    | 14   | 23   | nC    |
| Q <sub>gs</sub>     | Gate-Source Charge                             | V <sub>DS</sub> =50V                                     | -    | 4.5  | -    | nC    |
| Q <sub>gd</sub>     | Gate-Drain ("Miller") Charge                   | V <sub>GS</sub> =4.5V                                    | -    | 6.5  | -    | nC    |
| t <sub>d(on)</sub>  | Turn-on Delay Time                             | V <sub>DS</sub> =50V                                     | -    | 9.5  | -    | ns    |
| t <sub>r</sub>      | Rise Time                                      | I <sub>D</sub> =1A                                       | -    | 6    | -    | ns    |
| t <sub>d(off)</sub> | Turn-off Delay Time                            | R <sub>G</sub> =3.3Ω                                     | -    | 30   | -    | ns    |
| t <sub>f</sub>      | Fall Time                                      | V <sub>GS</sub> =10V                                     | -    | 65   | -    | ns    |
| C <sub>iss</sub>    | Input Capacitance                              | V <sub>GS</sub> =0V                                      | -    | 1350 | 2160 | pF    |
| C <sub>oss</sub>    | Output Capacitance                             | V <sub>DS</sub> =50V                                     | -    | 185  | -    | pF    |
| C <sub>rss</sub>    | Reverse Transfer Capacitance                   | f=1.0MHz   | -    | 10   | -    | pF    |
| R <sub>g</sub>      | Gate Resistance                                | f=1.0MHz   | -    | 1.6  | 3.2  | Ω     |

**Source-Drain Diode**

| Symbol          | Parameter                       | Test Conditions                           | Min. | Typ. | Max. | Units |
|-----------------|---------------------------------|---|------|------|------|-------|
| V <sub>SD</sub> | Forward On Voltage <sup>2</sup> | I <sub>S</sub> =2.9A, V <sub>GS</sub> =0V | -    | -    | 1.2  | V     |
| t <sub>rr</sub> | Reverse Recovery Time           | I <sub>S</sub> =7A, V <sub>GS</sub> =0V,  | -    | 48   | -    | ns    |
| Q <sub>rr</sub> | Reverse Recovery Charge         | dI/dt=100A/μs                             | -    | 65   | -    | nC    |

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> 2oz copper pad of FR4 board, t ≤10sec, 210°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

XSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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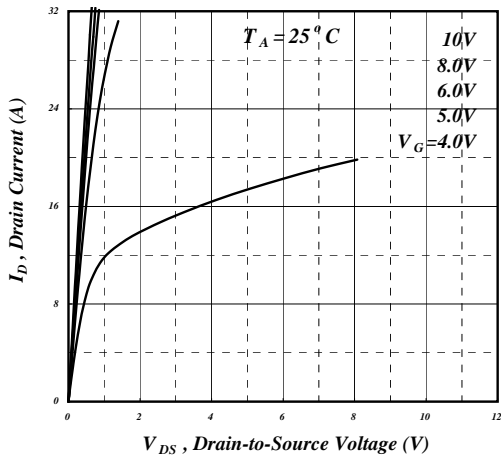


Fig 1. Typical Output Characteristics

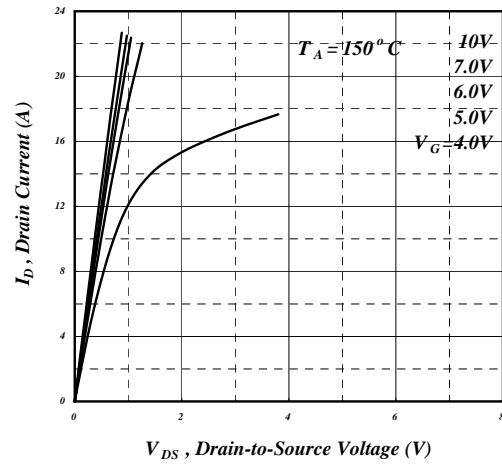


Fig 2. Typical Output Characteristics

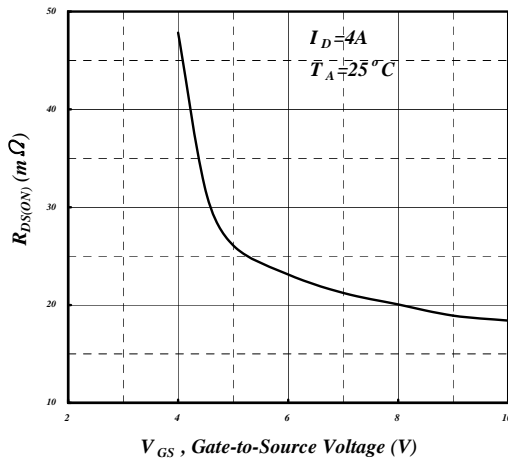


Fig 3. On-Resistance v.s. Gate Voltage

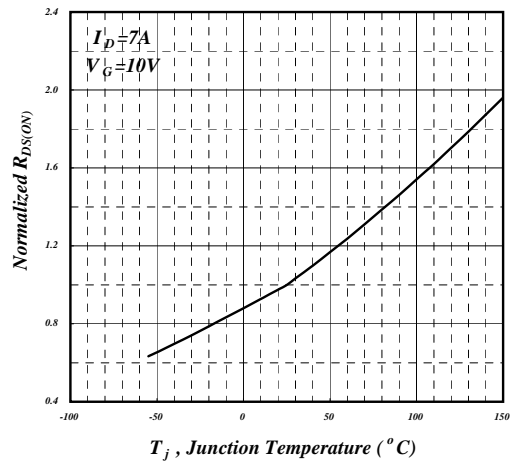


Fig 4. Normalized On-Resistance v.s. Junction Temperature

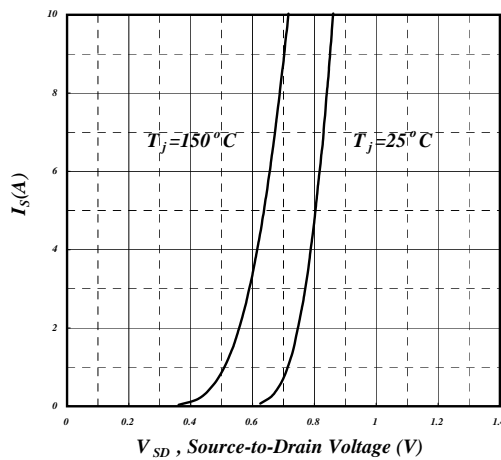


Fig 5. Forward Characteristic of Reverse Diode

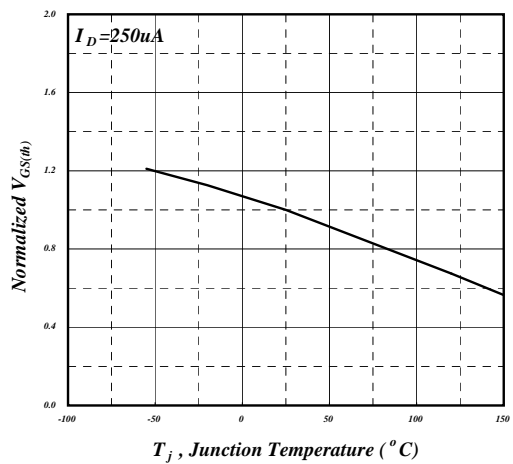
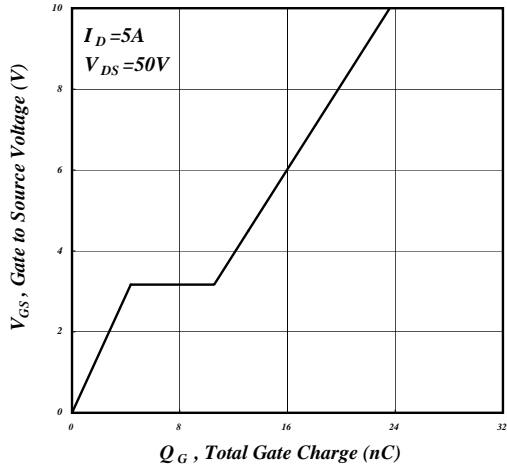
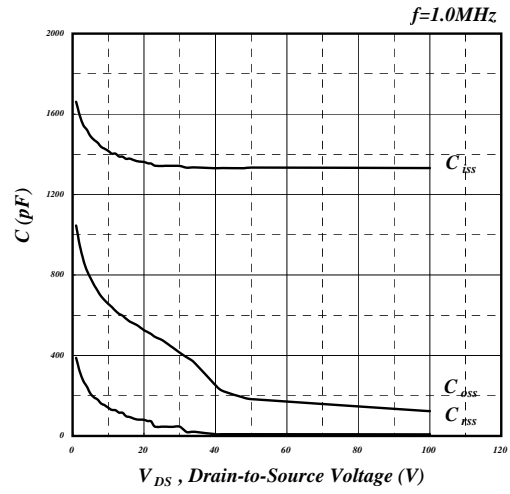


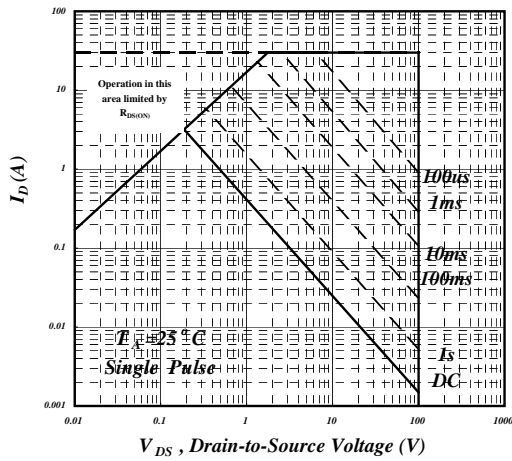
Fig 6. Gate Threshold Voltage v.s. Junction Temperature



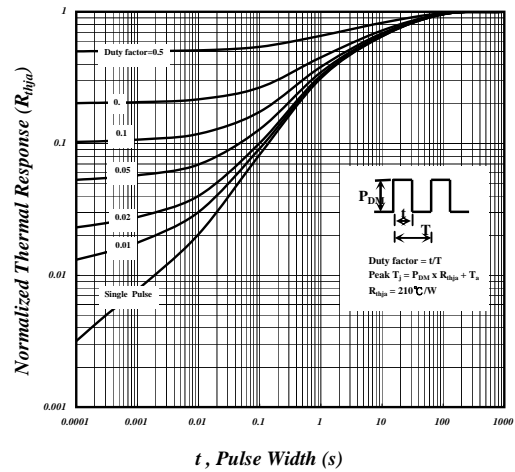
**Fig 7. Gate Charge Characteristics**



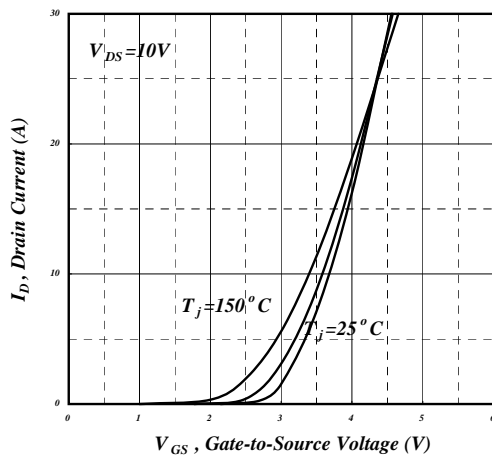
**Fig 8. Typical Capacitance Characteristics**



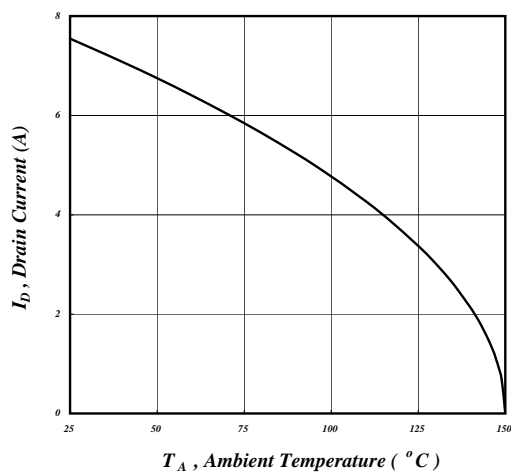
**Fig 9. Maximum Safe Operating Area**



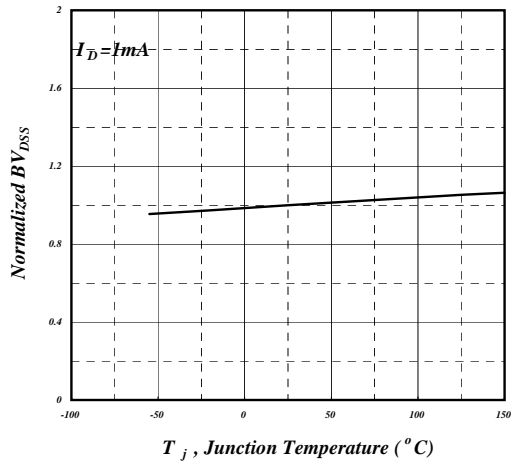
**Fig 10. Effective Transient Thermal Impedance**



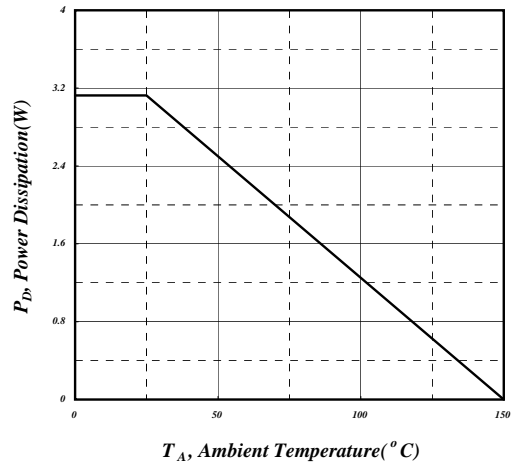
**Fig 11. Transfer Characteristics**



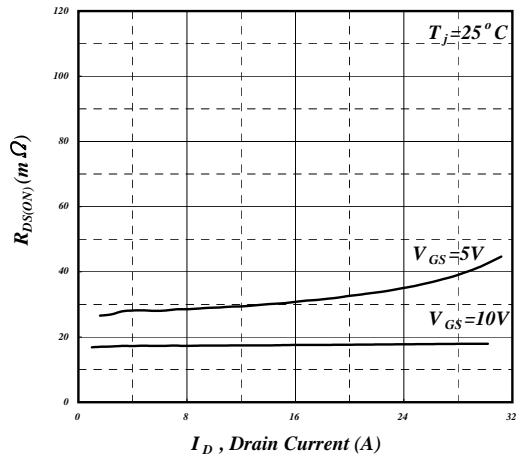
**Fig 12. Drain Current v.s. Ambient Temperature**



**Fig 13. Normalized  $BV_{DSS}$  v.s. Junction Temperature**



**Fig 14. Total Power Dissipation**



**Fig 15. Typ. Drain-Source on State Resistance**

**MARKING INFORMATION**